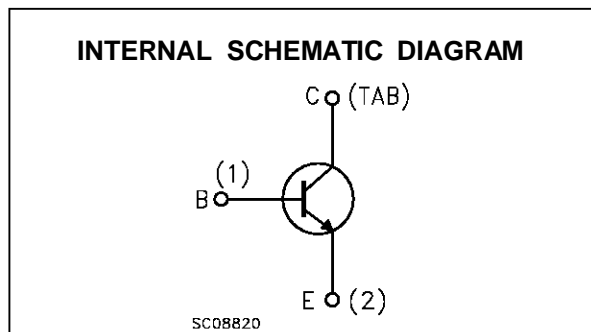
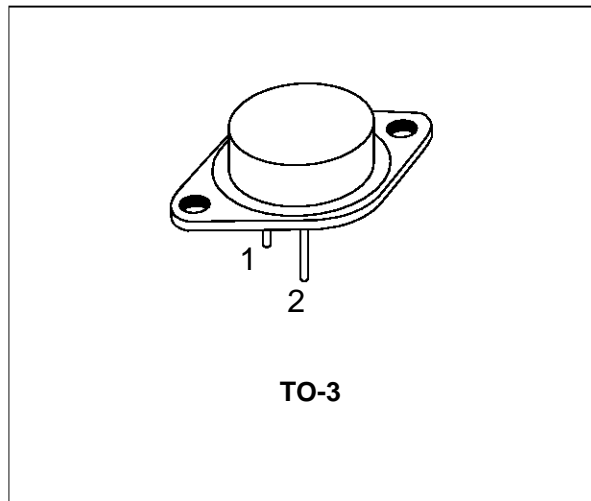


HIGH CURRENT NPN SILICON TRANSISTOR

■ SGS-THOMSON PREFERRED SALESTYPE

DESCRIPTION

The BUX12 is a silicon multiepitaxial planar NPN transistor in Jedec TO-3 metal case, intended for use in switching and linear applications in military and industrial equipment.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	300	V
V_{CEX}	Collector-emitter Voltage ($V_{BE} = -1.5V$)	300	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	250	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	20	A
I_{CM}	Collector Peak Current ($t_P = 10$ ms)	25	A
I_B	Base Current	4	A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25$ °C	150	W
T_{stg}	Storage Temperature	-65 to 200	°C
T_j	Max Operating Junction Temperature	200	°C

BUX12

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.17	°C/W
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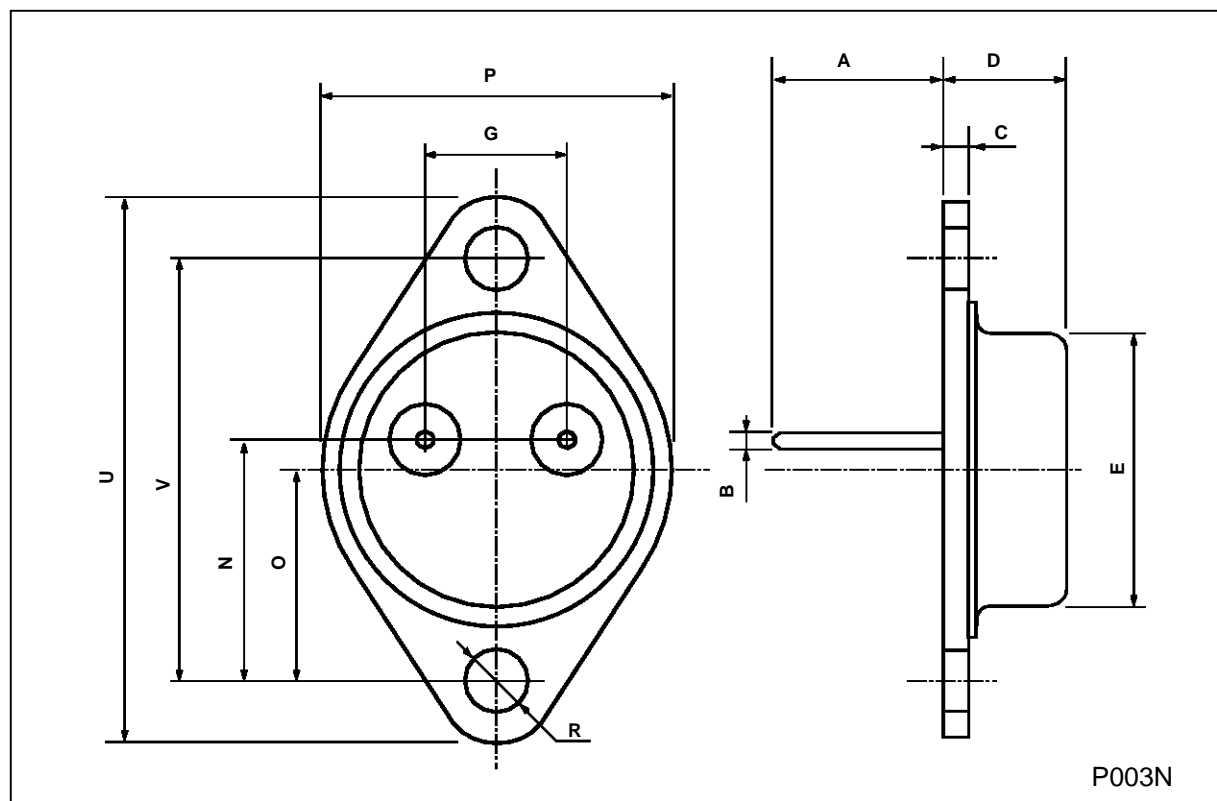
ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 200\text{ V}$			1.5	mA
I_{CEX}	Collector Cut-off Current	$V_{CE} = 300\text{ V}$ $T_{case} = 125\text{ °C}$ $V_{CE} = 300\text{ V}$			1.5	mA
		$V_{BE} = -1.5\text{ V}$ $V_{BE} = -1.5\text{ V}$			6	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			1	mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 200\text{ mA}$	250			V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	$I_E = 50\text{ mA}$	7			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{ A}$ $I_C = 10\text{ A}$		0.22 0.5	1 1.5	V V
		$I_B = 0.5\text{ A}$ $I_B = 1.25\text{ A}$				
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 10\text{ A}$		1.23	1.5	V
h_{FE}	DC Current Gain	$I_C = 5\text{ A}$ $I_C = 10\text{ A}$		20 10	60	
		$V_{CE} = 4\text{ V}$ $V_{CE} = 4\text{ V}$				
$I_{S/b}$	Second Breakdown Collector Current	$V_{CE} = 30\text{ V}$ $V_{CE} = 140\text{ V}$		5 0.15		A A
		$t = 1\text{ s}$ $t = 1\text{ s}$				
f_T	Transistor Frequency	$I_C = 1\text{ A}$ $f = 10\text{ MHz}$		8		MHz
t_{on}	Turn-on Time See fig.2	$I_C = 10\text{ A}$ $V_{CC} = 150\text{ V}$			0.28 1	μs
t_s	Storage Time See fig.2	$I_C = 10\text{ A}$			1.45	μs
t_f	Fall Time See fig.2	$I_{B2} = -1.25\text{ A}$ $V_{CC} = 150\text{ V}$			0.23	μs
	Clamped $E_{s/b}$ Collector Current	$V_{clamp} = 250\text{ V}$ $L = 500\text{ }\mu\text{H}$	10			A

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

TO-3 (H) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		11.7			0.460	
B	0.96		1.10	0.037		0.043
C			1.70			0.066
D			8.7			0.342
E			20.0			0.787
G		10.9			0.429	
N		16.9			0.665	
P			26.2			1.031
R	3.88		4.09	0.152		0.161
U			39.50			1.555
V		30.10			1.185	



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